Low-power dual Schmitt trigger inverter Rev. 5 — 4 December 2012

Product data sheet

General description 1.

The 74AUP2G14 provides two inverting buffers with Schmitt trigger action which accept standard input signals. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial power-down applications using IOFF. The IOFF circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The inputs switch at different points for positive and negative-going signals. The difference between the positive voltage V_{T+} and the negative voltage V_{T-} is defined as the input hysteresis voltage V_H.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78 Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Applications 3.

- Wave and pulse shaper
- Astable multivibrator
- Monostable multivibrator



Low-power dual Schmitt trigger inverter

4. Ordering information

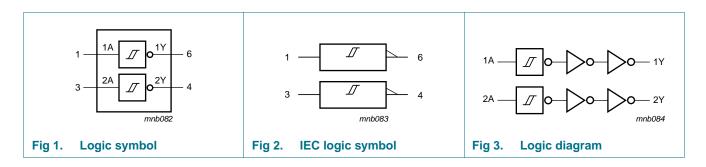
Table 1. Ordering information									
Type number	Package	Package							
	Temperature range	Name	Description	Version					
74AUP2G14GW	–40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363					
74AUP2G14GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1.45 \times 0.5 mm	SOT886					
74AUP2G14GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body 1 \times 1 \times 0.5 mm	SOT891					
74AUP2G14GN	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $0.9 \times 1.0 \times 0.35$ mm	SOT1115					
74AUP2G14GS	–40 °C to +125 °C	XSON6	extremely thin small outline package; no leads; 6 terminals; body $1.0 \times 1.0 \times 0.35$ mm	SOT1202					

5. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74AUP2G14GW	рК
74AUP2G14GM	рК
74AUP2G14GF	рК
74AUP2G14GN	рК
74AUP2G14GS	рК

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

6. Functional diagram

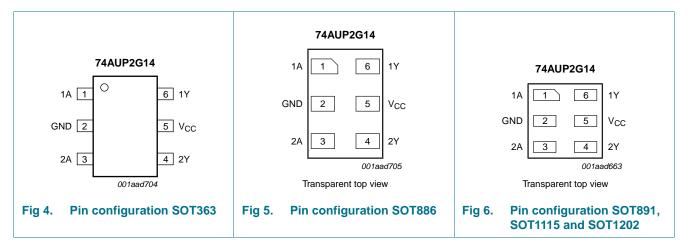


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7. Pinning information

7.1 Pinning



7.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V _{CC}	5	supply voltage
1Y	6	data output

8. Functional description

Table 4.Function table^[1]

Input	Output
nA	nY
L	Н
Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

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Limiting values 9.

Limiting values Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{O} = 0 V$ to V_{CC}	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 packages: above 87.5 °C the value of Ptot derates linearly with 4.0 mW/K.

For XSON6 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

10. Recommended operating conditions

Table 6.	Recommended operating co	onditions			
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C

11. Static characteristics

Table 7. **Static characteristics**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Parameter	Conditions	Min	Тур	Max	Unit
5 °C					
HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
	I_O = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
	$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.75\times V_{CC}$	-	-	V
	$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
	$I_{O} = -1.9 \text{ mA}; \text{ V}_{CC} = 1.65 \text{ V}$	1.32	-	-	V
	$I_0 = -2.3 \text{ mA}; \text{ V}_{CC} = 2.3 \text{ V}$	2.05	-	-	V
	$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
	$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
	$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
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ata sheet	Rev. 5 — 4 December 2012				4 of 21
	5°C HIGH-level output voltage	$\begin{array}{l} \textbf{Figh-level output voltage} & V_{I} = V_{T+} \text{ or } V_{T-} \\ \hline I_{O} = -20 \ \mu\text{A}; \ V_{CC} = 0.8 \ \text{V to } 3.6 \ \text{V} \\ \hline I_{O} = -1.1 \ \text{mA}; \ V_{CC} = 1.1 \ \text{V} \\ \hline I_{O} = -1.7 \ \text{mA}; \ V_{CC} = 1.4 \ \text{V} \\ \hline I_{O} = -1.9 \ \text{mA}; \ V_{CC} = 1.65 \ \text{V} \\ \hline I_{O} = -2.3 \ \text{mA}; \ V_{CC} = 2.3 \ \text{V} \\ \hline I_{O} = -3.1 \ \text{mA}; \ V_{CC} = 2.3 \ \text{V} \\ \hline I_{O} = -2.7 \ \text{mA}; \ V_{CC} = 3.0 \ \text{V} \\ \hline I_{O} = -4.0 \ \text{mA}; \ V_{CC} = 3.0 \ \text{V} \\ \hline \text{All information provided in this document is subject to legal disclaimers.} \end{array}$	S °C HIGH-level output voltage $V_I = V_{T+}$ or V_{T-} $I_O = -20 \ \mu A; \ V_{CC} = 0.8 \ V \ to \ 3.6 \ V$ $V_{CC} - 0.1$ $I_O = -1.1 \ mA; \ V_{CC} = 1.1 \ V$ $0.75 \times V_{CC}$ $I_O = -1.7 \ mA; \ V_{CC} = 1.4 \ V$ 1.11 $I_O = -1.9 \ mA; \ V_{CC} = 1.65 \ V$ 1.32 $I_O = -2.3 \ mA; \ V_{CC} = 2.3 \ V$ 2.05 $I_O = -3.1 \ mA; \ V_{CC} = 2.3 \ V$ 1.9 $I_O = -2.7 \ mA; \ V_{CC} = 3.0 \ V$ 2.72 $I_O = -4.0 \ mA; \ V_{CC} = 3.0 \ V$ 2.6 All information provided in this document is subject to legal disclaimers.	S°C VI = VT+ or VT- Io = -20 μ A; VCC = 0.8 V to 3.6 V VCC - 0.1 - Io = -1.1 mA; VCC = 1.1 V 0.75 × VCC - Io = -1.7 mA; VCC = 1.4 V 1.11 - Io = -1.9 mA; VCC = 1.65 V 1.32 - Io = -2.3 mA; VCC = 2.3 V 2.05 - Io = -3.1 mA; VCC = 3.0 V 2.72 - Io = -4.0 mA; VCC = 3.0 V 2.6 - All information provided in this document is subject to legal disclaimers.	S °C HIGH-level output voltage $V_I = V_{T+}$ or V_{T-} $I_O = -20 \ \mu A; \ V_{CC} = 0.8 \ V \ to \ 3.6 \ V$ $V_{CC} - 0.1 \ -$ - $I_O = -1.1 \ mA; \ V_{CC} = 1.1 \ V$ $0.75 \times V_{CC} \ -$ - $I_O = -1.7 \ mA; \ V_{CC} = 1.4 \ V$ $1.11 \ -$ - $I_O = -1.9 \ mA; \ V_{CC} = 1.65 \ V$ $1.32 \ -$ - $I_O = -2.3 \ mA; \ V_{CC} = 2.3 \ V$ $2.05 \ -$ - $I_O = -3.1 \ mA; \ V_{CC} = 2.3 \ V$ $1.9 \ -$ - $I_O = -2.7 \ mA; \ V_{CC} = 3.0 \ V$ $2.72 \ -$ - $I_O = -4.0 \ mA; \ V_{CC} = 3.0 \ V$ $2.6 \ -$ - All information provided in this document is subject to legal disclaimers. $\Phi NXP \ B.V. 2012.$

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74AUP2G14

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Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.31	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.44	V
I.	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.1	μΑ
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.2	μΑ
∆l _{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.2	μA
СС	supply current	V_{I} = GND or $V_{CC};I_{O}$ = 0 A; V_{CC} = 0.8 V to 3.6 V		-	0.5	μA
∆l _{CC}	additional supply current				40	μA
CI	input capacitance	$V_I = GND \text{ or } V_{CC}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	1.1	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.7	-	pF
T _{amb} = –	40 °C to +85 °C					
V _{он}	HIGH-level output voltage	$V_{I} = V_{T+}$ or V_{T-}				
		I_{O} = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.7\times V_{CC}$	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.30	-	-	V
		I_{O} = -2.3 mA; V_{CC} = 2.3 V	1.97	-	-	V
		I_{O} = -3.1 mA; V_{CC} = 2.3 V	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		I_{O} = -4.0 mA; V_{CC} = 3.0 V	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+} \text{ or } V_{T-}$				
		I_{O} = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_0 = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	$0.3\times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I_{O} = 1.9 mA; V_{CC} = 1.65 V	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.45	V
I	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.5	μA
OFF	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.5	μA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μA
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
∆l _{CC}	additional supply current		-	-	50	μA
T _{amb} = -	40 °C to +125 °C					
V _{ОН}	HIGH-level output voltage	$V_I = V_{T+} \text{ or } V_{T-}$				
		I_{O} = –20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	$0.6 \times V_{\text{CC}}$	-	-	V
		$I_0 = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_0 = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_0 = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_0 = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_0 = -4.0 \text{ mA}; \text{ V}_{CC} = 3.0 \text{ V}$	2.30	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{T+}$ or V_{T-}				
		I_O = 20 $\mu\text{A};V_{CC}$ = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	$0.33 \times V_{CC}$	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.41	V
		$I_0 = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
l _l	input leakage current	$V_I = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_{I} or V_{O} = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V};$		-	±0.75	μA
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μA
ΔI_{CC}	additional supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} - 0.6 \; V; \; I_{O} = 0 \; A; \\ V_{CC} = 3.3 \; V \end{array}$	-	-	75	μΑ

Table 7. Static characteristics ...continued

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12. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions			25 °C		_4	10 °C to +1	25 °C	Unit
				lin	Typ[1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F							1		
^t pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	19.9	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2	2.7	5.9	11.0	2.4	11.1	11.2	ns
		V_{CC} = 1.4 V to 1.6 V	2	2.6	4.3	6.6	2.4	7.1	7.4	ns
		V_{CC} = 1.65 V to 1.95 V	2	2.1	3.7	5.4	2.0	6.0	6.2	ns
		V_{CC} = 2.3 V to 2.7 V	2	2.0	3.0	4.1	1.7	4.5	4.7	ns
		V_{CC} = 3.0 V to 3.6 V	1	1.9	2.8	3.6	1.5	3.9	4.0	ns
C _L = 10	ρF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	23.4	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	2	<u>2.9</u>	6.8	12.7	2.8	12.8	12.9	ns
		V_{CC} = 1.4 V to 1.6 V	2	2.8	5.0	7.7	2.6	8.2	8.6	ns
		V_{CC} = 1.65 V to 1.95 V	2	2.7	4.2	6.2	2.5	6.7	7.1	ns
		V_{CC} = 2.3 V to 2.7 V	2	2.3	3.6	4.8	2.1	5.2	5.5	ns
		V_{CC} = 3.0 V to 3.6 V	2	2.1	3.3	4.3	2.0	4.5	4.7	ns
C _L = 15	ρF									
pd	propagation delay	nA to nY; see <u>Figure 7</u>	[2]							
		$V_{CC} = 0.8 V$		-	26.9	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	3	3.3	7.6	14.3	3.0	14.5	14.7	ns
		V_{CC} = 1.4 V to 1.6 V	3	3.3	5.5	8.6	2.9	9.4	9.8	ns
		V_{CC} = 1.65 V to 1.95 V	2	2.8	4.7	7.0	2.8	7.7	8.1	ns
		V_{CC} = 2.3 V to 2.7 V	2	2.7	4.0	5.5	2.4	5.9	6.2	ns
		V_{CC} = 3.0 V to 3.6 V	2	2.6	3.8	4.8	2.2	5.2	5.4	ns
C _L = 30	ρF									
pd	propagation delay	nA to nY; see Figure 7	[2]							
		$V_{CC} = 0.8 V$		-	37.3	-	-	-	-	ns
		V_{CC} = 1.1 V to 1.3 V	4	1.0	9.8	18.7	3.9	19.6	20.0	ns
		V_{CC} = 1.4 V to 1.6 V	3	3.7	7.1	11.2	3.8	12.3	12.9	ns
		V_{CC} = 1.65 V to 1.95 V	3	3.6	6.0	9.1	3.6	10.0	10.6	ns
		V_{CC} = 2.3 V to 2.7 V	3	3.5	5.2	6.9	3.2	7.5	7.9	ns
		V_{CC} = 3.0 V to 3.6 V	3	3.3	4.8	6.1	3.1	7.1	7.4	ns

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-40 °C to +125 °C Conditions 25 °C Symbol Parameter Unit Min Typ[1] Max Min Max Max (85 °C) (125 °C) C_L = 5 pF, 10 pF, 15 pF and 30 pF [3][4] $f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ power dissipation CPD capacitance $V_{CC} = 0.8 V$ 2.6 pF _ pF $V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$ 2.7 _ -_ -_ $V_{CC} = 1.4 \text{ V to } 1.6 \text{ V}$ 2.9 pF ---_ _ $V_{CC} = 1.65 \text{ V}$ to 1.95 V 3.1 pF ----- $V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$ 3.7 pF _ --_ - $V_{CC} = 3.0 \text{ V}$ to 3.6 V 4.3 pF _ _ -_ _

Table 8. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

[1] All typical values are measured at nominal V_{CC}.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_{D} in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 $f_i = input frequency in MHz;$

 f_0 = output frequency in MHz;

C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of the outputs.

13. Waveforms

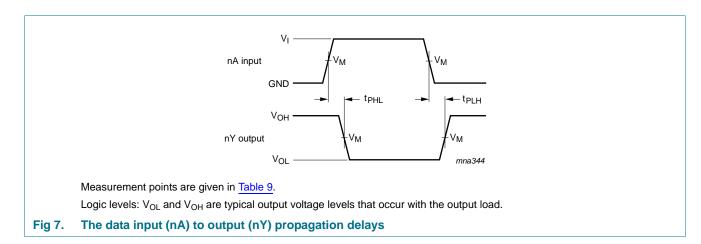


Table 9. **Measurement points**

Supply voltage	Output	Input				
V _{CC}	V _M	V _M	VI	$t_r = t_f$		
0.8 V to 3.6 V	$0.5 imes V_{CC}$	$0.5 imes V_{CC}$	V _{CC}	≤ 3.0 ns		

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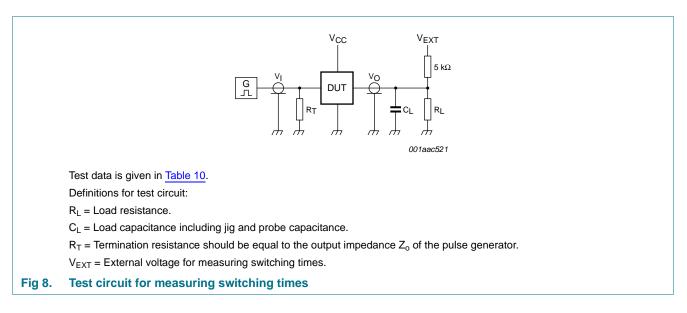


Table 10. Test data

Supply voltage	Load V		V _{EXT}		
V _{cc}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 k Ω or 1 M Ω	open	GND	$2 \times V_{CC}$

[1] For measuring enable and disable times $R_L = 5 \text{ k}\Omega$, for measuring propagation delays, set-up and hold times and pulse width $R_L = 1 \text{ M}\Omega$.

14. Transfer characteristics

Table 11. Transfer characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 8.

Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	_
	positive-going threshold voltage	see Figure 9 and Figure 10							
		$V_{CC} = 0.8 V$	0.30	-	0.60	0.30	0.60	0.62	V
		$V_{CC} = 1.1 V$	0.53	-	0.90	0.53	0.90	0.92	V
		V _{CC} = 1.4 V	0.74	-	1.11	0.74	1.11	1.13	V
		V _{CC} = 1.65 V	0.91	-	1.29	0.91	1.29	1.31	V
		$V_{CC} = 2.3 V$	1.37	-	1.77	1.37	1.77	1.80	V
		$V_{CC} = 3.0 V$	1.88	-	2.29	1.88	2.29	2.32	V
V _{T-}	negative-going threshold voltage	see Figure 9 and Figure 10							
		$V_{CC} = 0.8 V$	0.10	-	0.60	0.10	0.60	0.60	V
		V _{CC} = 1.1 V	0.26	-	0.65	0.26	0.65	0.65	V
		$V_{CC} = 1.4 V$	0.39	-	0.75	0.39	0.75	0.75	V
		V _{CC} = 1.65 V	0.47	-	0.84	0.47	0.84	0.84	V
		$V_{CC} = 2.3 V$	0.69	-	1.04	0.69	1.04	1.04	V
		$V_{CC} = 3.0 V$	0.88	-	1.24	0.88	1.24	1.24	V

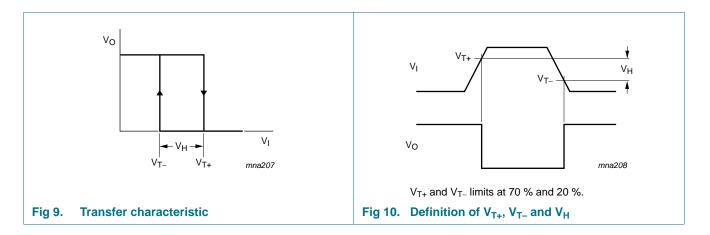


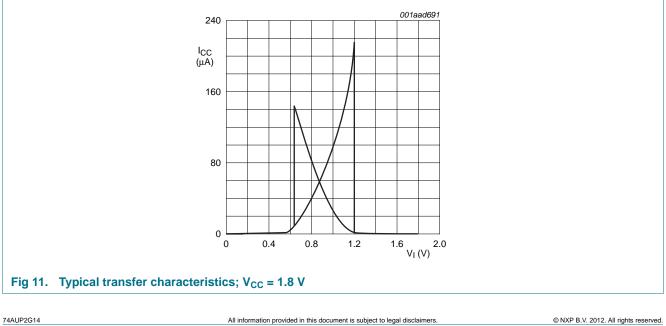
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Symbol	Parameter	Conditions		25 °C			–40 °C to +125 °C		
			Min	Тур	Мах	Min	Max (85 °C)	Max (125 °C)	
V _H	hysteresis voltage	$(V_{T+} - V_{T-})$; see <u>Figure 9</u> , <u>Figure 10</u> , <u>Figure 11</u> and <u>Figure 12</u>						'	
		$V_{CC} = 0.8 V$	0.07	-	0.50	0.07	0.50	0.50	V
		V _{CC} = 1.1 V	0.08	-	0.46	0.08	0.46	0.46	V
		$V_{CC} = 1.4 V$	0.18	-	0.56	0.18	0.56	0.56	V
		V _{CC} = 1.65 V	0.27	-	0.66	0.27	0.66	0.66	V
		$V_{CC} = 2.3 V$	0.53	-	0.92	0.53	0.92	0.92	V
		$V_{CC} = 3.0 V$	0.79	-	1.31	0.79	1.31	1.31	V

Table 11. Transfer characteristics ...continued

15. Waveforms transfer characteristics

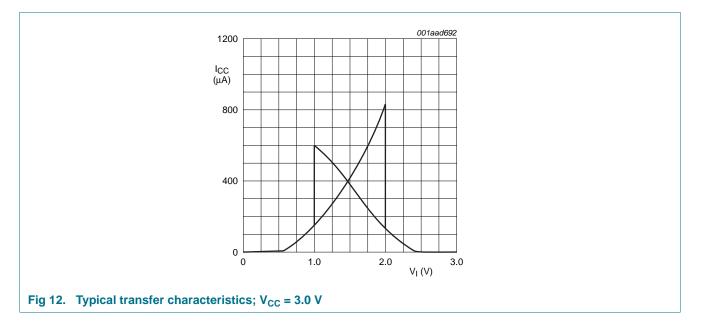




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16. Application information

The slow input rise and fall times cause additional power dissipation, this can be calculated using the following formula:

 $P_{add} = f_i \times (t_r \times \Delta I_{CC(AV)} + t_f \times \Delta I_{CC(AV)}) \times V_{CC}$ where:

 P_{add} = additional power dissipation (μ W);

 $f_i = input frequency (MHz);$

 t_r = rise time (ns); 10 % to 90 %;

t_f = fall time (ns); 90 % to 10 %;

 $\Delta I_{CC(AV)}$ = average additional supply current (µA).

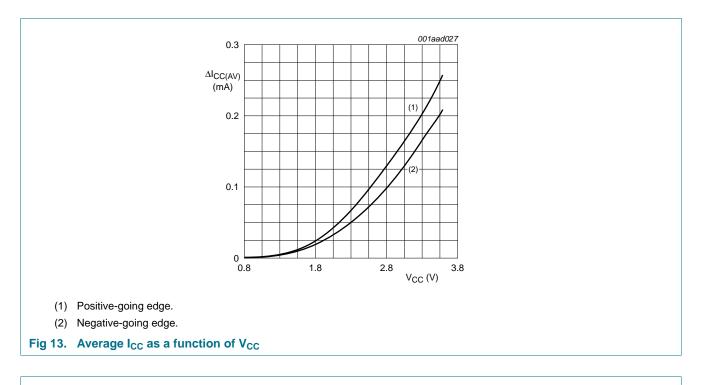
Average $\Delta I_{CC(AV)}$ differs with positive or negative input transitions, as shown in Figure 13.

An example of a relaxation circuit using the 74AUP2G14 is shown in Figure 14.

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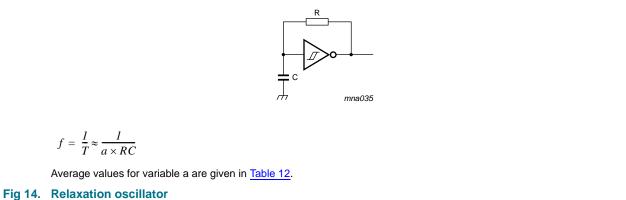


Table 12. Variable values

Supply voltage	Variable a	
1.1 V	1.28	
1.5 V	1.22	
1.8 V	1.24	
2.8 V	1.34	
3.3 V	1.45	

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17. Package outline

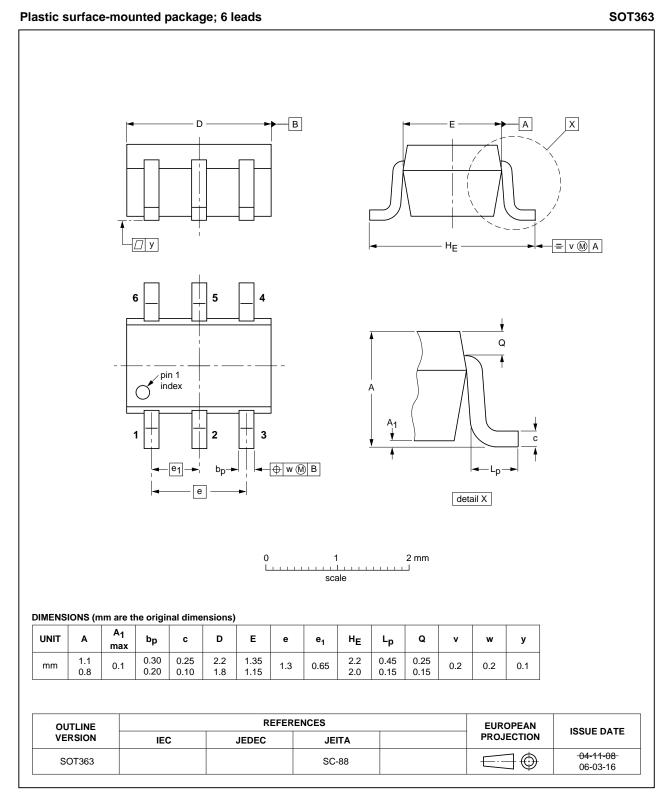


Fig 15. Package outline SOT363 (SC-88)

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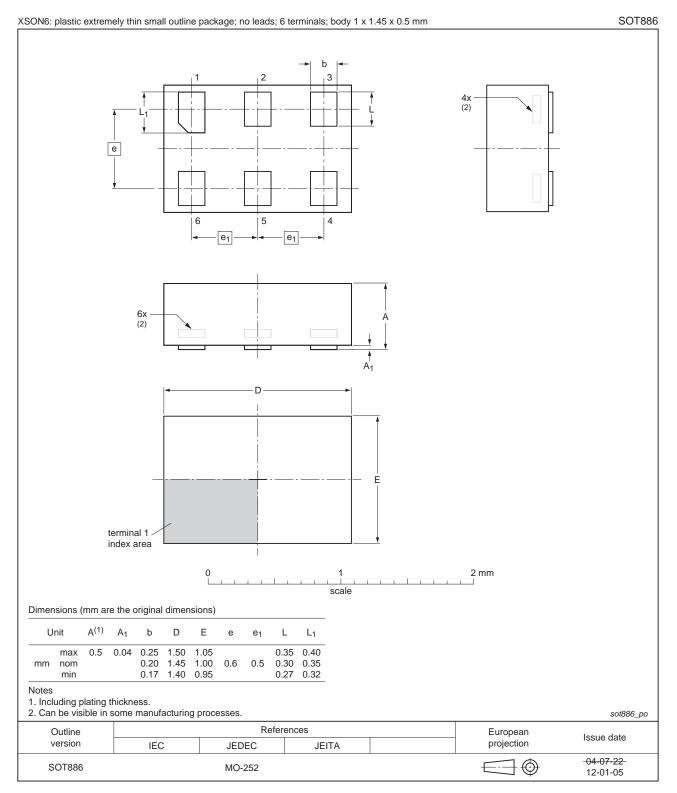
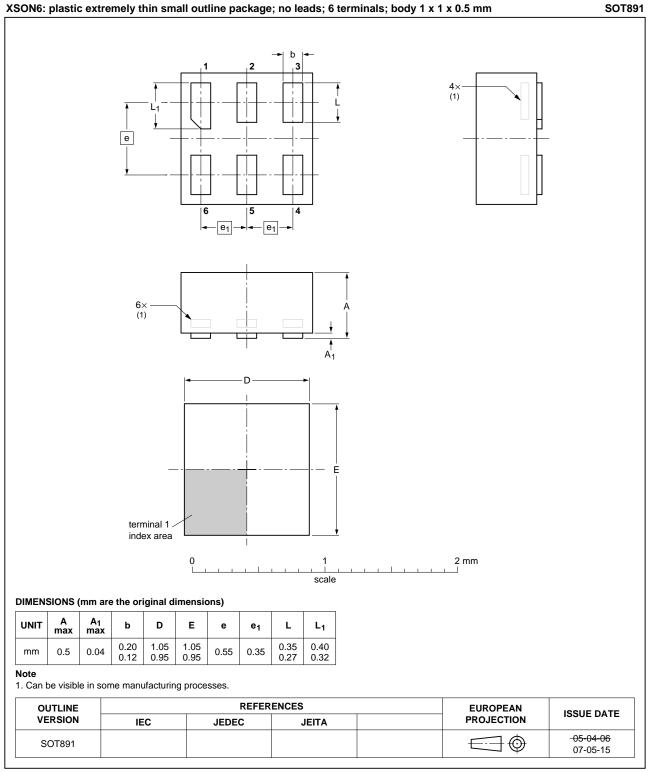


Fig 16. Package outline SOT886 (XSON6)

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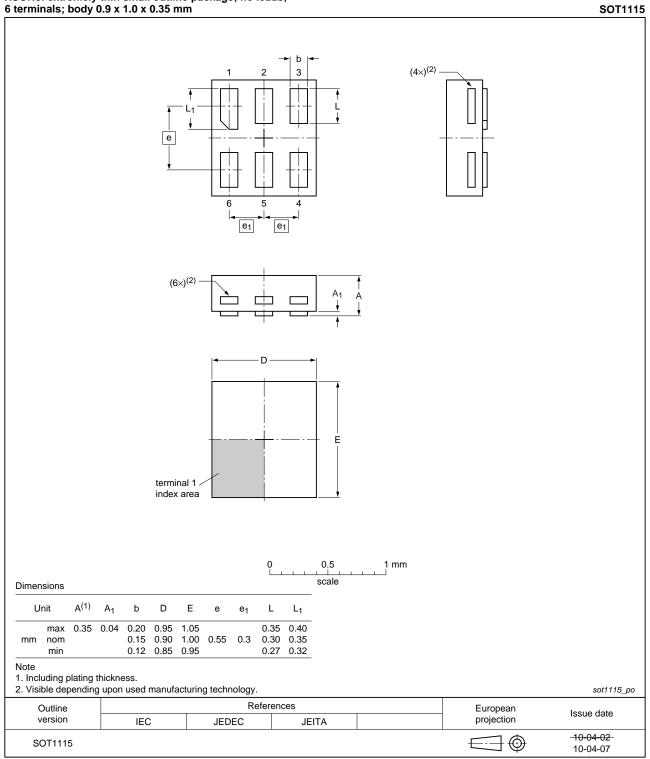


XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

Fig 17. Package outline SOT891 (XSON6)

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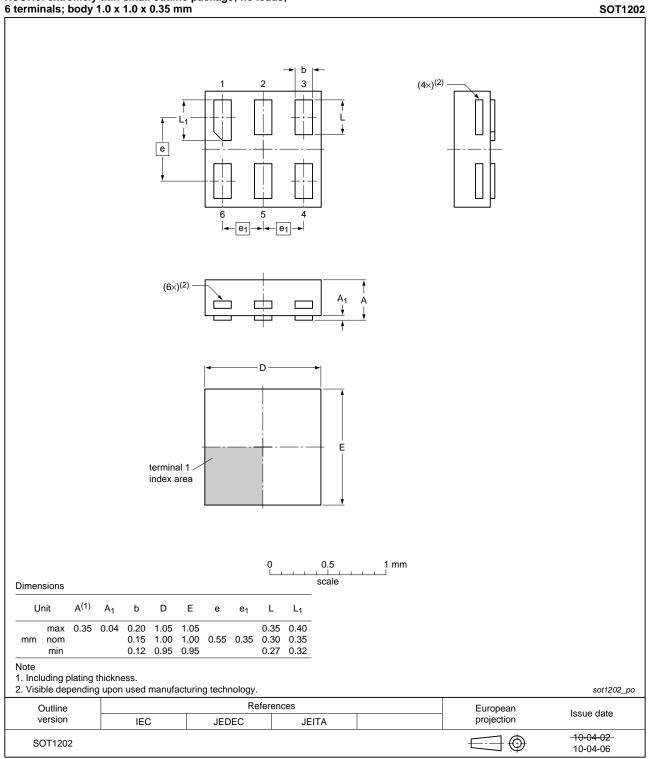
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XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 18. Package outline SOT1115 (XSON6)

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XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

Fig 19. Package outline SOT1202 (XSON6)

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18. Abbreviations

Acronym CDM DUT	Description Charged Device Model
	-
DOT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

19. Revision history

Table 14. Revision history **Document ID Release date** Data sheet status Change notice Supersedes 74AUP2G14 v.5 20121204 Product data sheet 74AUP2G14 v.4 Modifications: • Package outline drawing of SOT886 (Figure 16) modified. 74AUP2G14 v.4 20111201 Product data sheet 74AUP2G14 v.3 -74AUP2G14 v.3 20100722 Product data sheet 74AUP2G14 v.2 -74AUP2G14 v.2 20090703 Product data sheet 74AUP2G14 v.1 -74AUP2G14 v.1 20061219 Product data sheet --

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